THE MECHANISM OF INFLUENCE OF RESIDUAL THERMAL STRESSES ON THE ELECTROPHYSICAL PROPERTIES OF COMPOSITE FILMS ON THE BASIS OF SnO₂-Sb

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Summary

The influence of residual thermal stresses, resulting from the mismatch of the thermal expansion coefficients of components, on the electrophysical properties of composite films on the basis of SnO_2 -Sb is investigated. The dependences of all the investigated properties on the degree of mismatch have an extremum, which corresponds to the maximum of residual stresses. The major factors of such an influence are established on the basis of literary data and the obtained results.